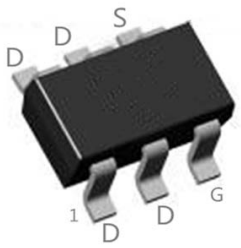
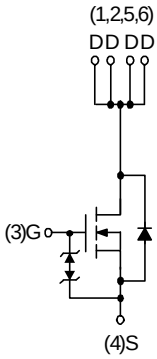
Features

- 200V/1.2A,
  $R_{DS(ON)}$= 680mΩ(max.) @ V_{GS}=10V
- ESD Protection
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
  (RoHS Compliant)

Pin Configuration





N-Channel MOSFET

Applications

- DC-DC converter for Networking.
- Load switch.

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V_{DSS}	Drain-Source Voltage		200	V
V_{GSS}	Gate-Source Voltage		±25	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	
I_S	Diode Continuous Forward Current	T_A=25°C	1.2	A
I_D	Continuous Drain Current	T_A=25°C	1.2	A
		T_A=70°C	0.96	
I_{DM} [a]	Pulsed Drain Current	T_A=25°C	4.8	A
P_D	Maximum Power Dissipation	T_A=25°C	2.5	W
		T_A=70°C	1.6	
$R_{\theta JA}$ [c]	Thermal Resistance-Junction to Ambient	t ≤ 10s	50	°C/W
		Steady State	90	°C/W
I_{AS} [b]	Avalanche Current, Single pulse	L=0.5mH	1	A
E_{AS} [b]	Avalanche Energy, Single pulse	L=0.5mH	0.25	mJ

Note a：Pulse width limited by max. junction temperature.
Note b：UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_j=25°C).
Note c：Surface mounted on 1in^2 pad area.

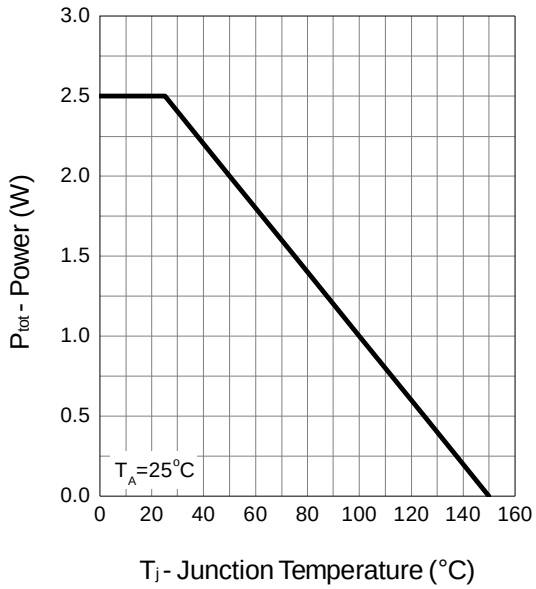
Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	200	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=160V, V_{GS}=0V	-	-	1	μA
		T_J=85°C	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	3	4	5	V
I_{GSS}	Gate Leakage Current	V_{GS}=±25V, V_{DS}=0V	-	-	±10	μA
$R_{DS(ON)}$ [d]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=1A	-	570	680	mΩ
Diode Characteristics						
V_{SD} [d]	Diode Forward Voltage	I_{SD}=1A, V_{GS}=0V	-	0.8	1.3	V
t_{rr}	Reverse Recovery Time	I_{SD}=1A, dI_{SD}/dt=100A/μs	-	48	-	ns
Q_{rr}	Reverse Recovery Charge		-	70	-	nC
Dynamic Characteristics [e]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,f=1MHz	-	4	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=30V, Frequency=1.0MHz	-	280	-	pF
C_{oss}	Output Capacitance		-	25	-	
C_{rss}	Reverse Transfer Capacitance		-	8.5	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=30V, R_L=30Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω	-	10	18	ns
t_r	Turn-on Rise Time		-	8	15	
$t_{d(OFF)}$	Turn-off Delay Time		-	9	17	
t_f	Turn-off Fall Time		-	2	4	
Gate Charge Characteristics [e]						
Q_g	Total Gate Charge	V_{DS}=100V, V_{GS}=10V, I_{DS}=1A	-	6	9	nC
Q_{gs}	Gate-Source Charge		-	2	-	
Q_{gd}	Gate-Drain Charge		-	1.5	-	

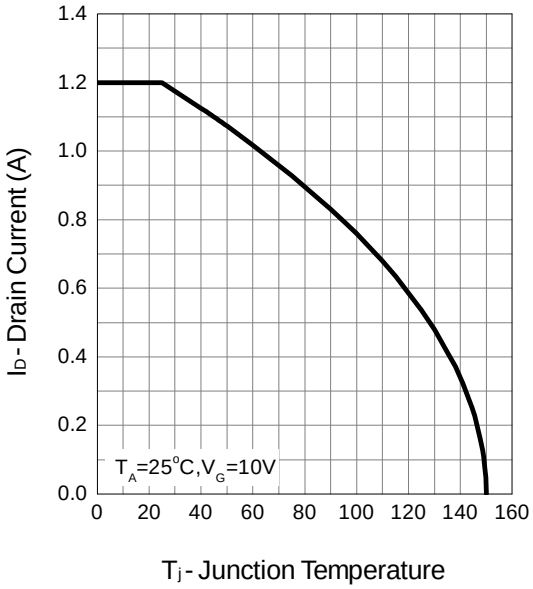
Note d：Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note e：Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

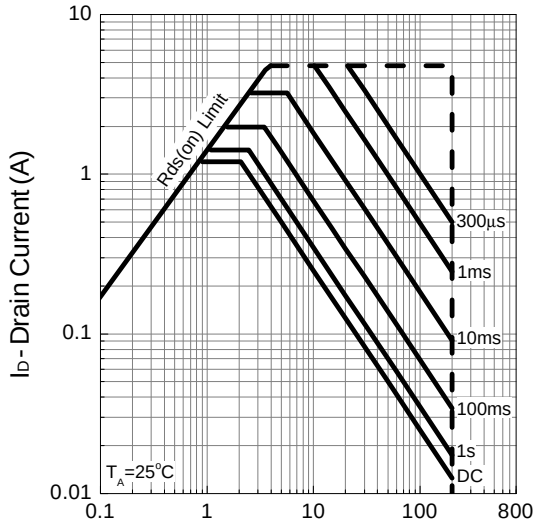
Power Dissipation



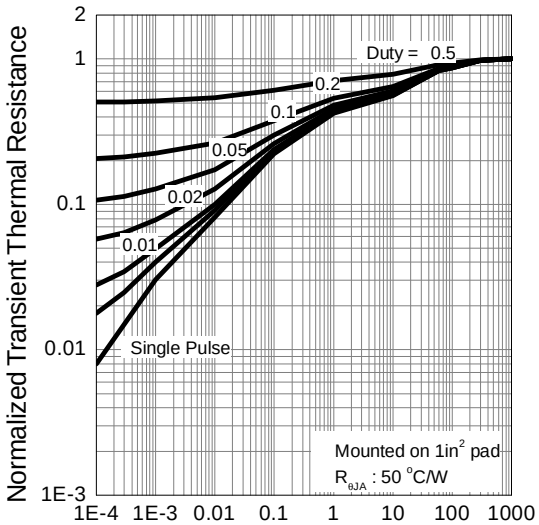
Drain Current



Safe Operation Area

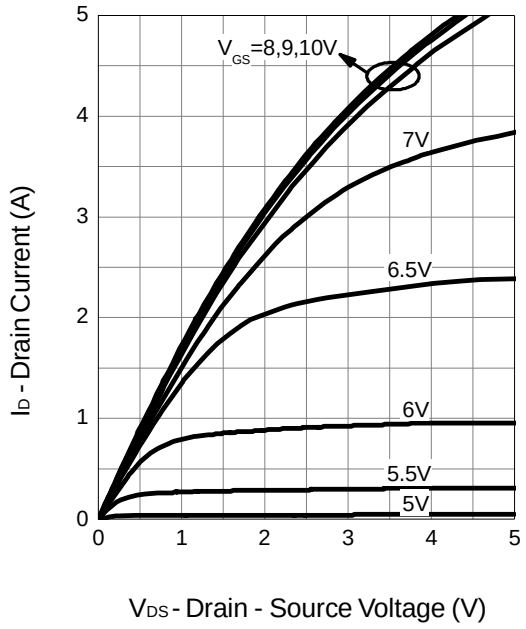


Thermal Transient Impedance

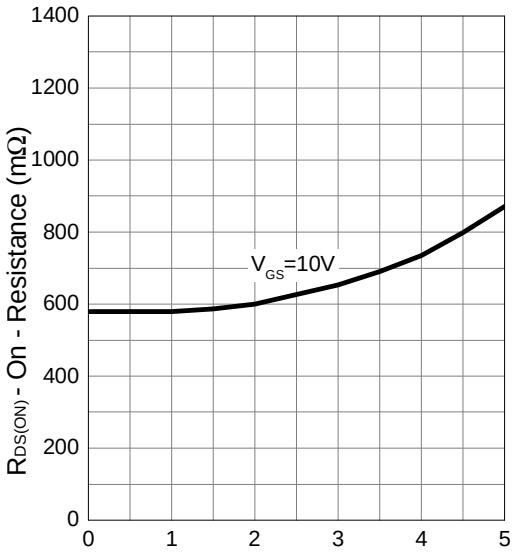


Typical Operating Characteristics (Cont.)

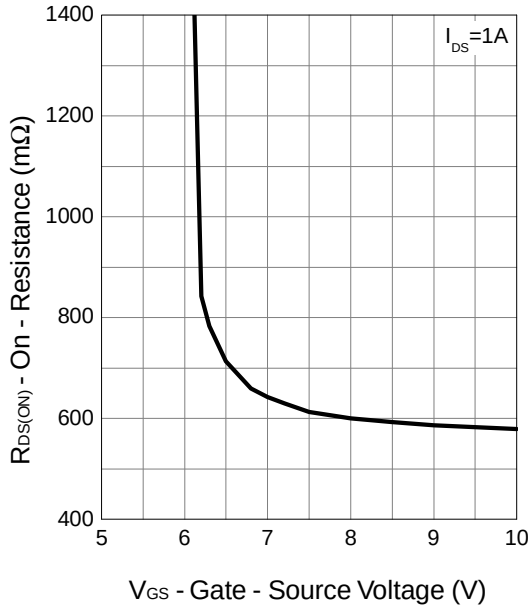
Output Characteristics



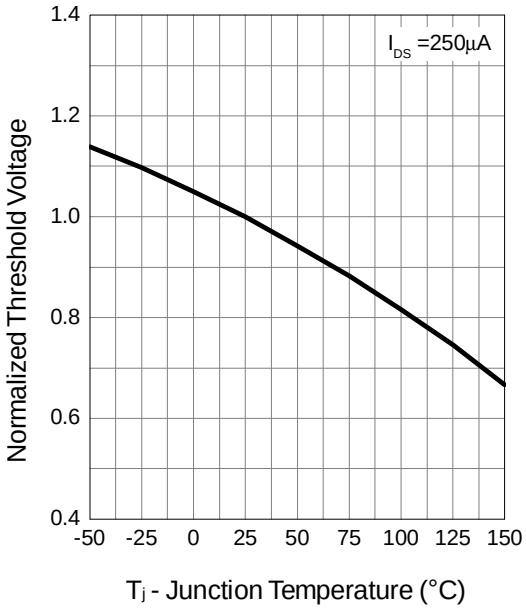
Drain-Source On Resistance



Gate-Source On Resistance

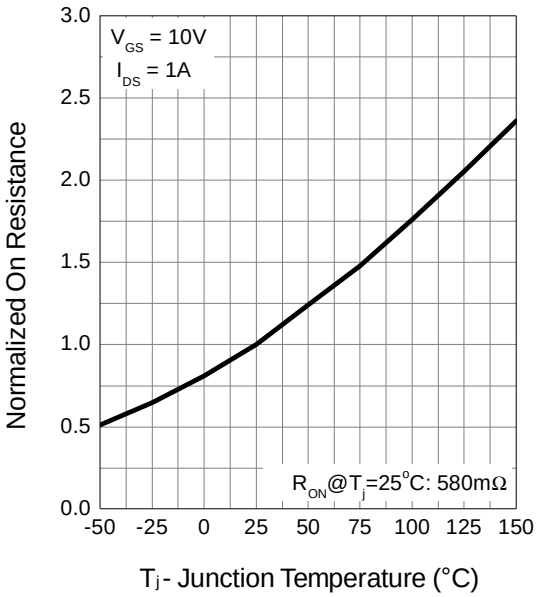


Gate Threshold Voltage

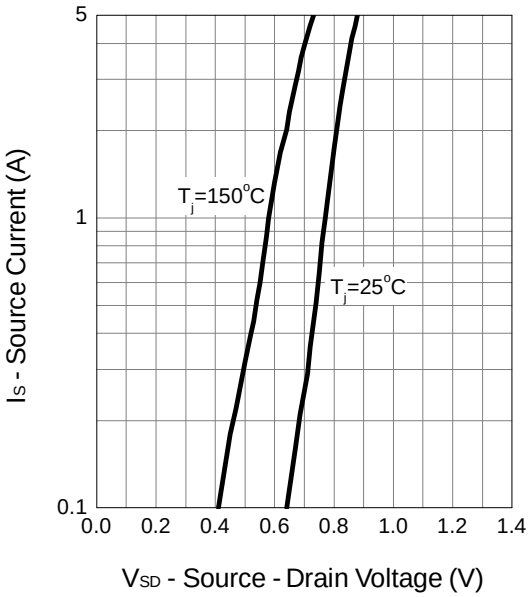


Typical Operating Characteristics (Cont.)

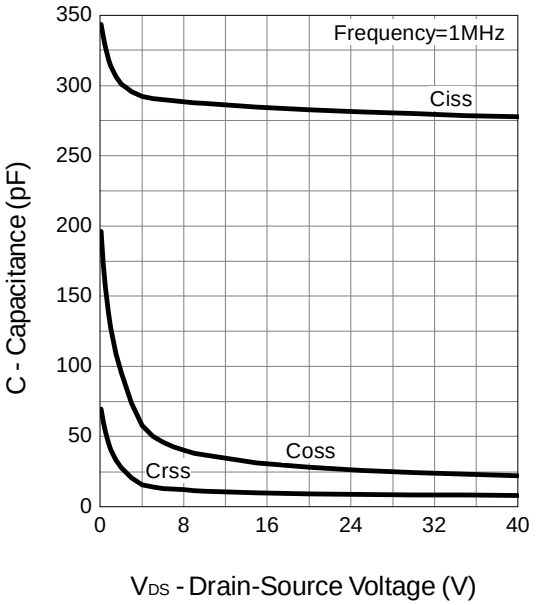
Drain-Source On Resistance



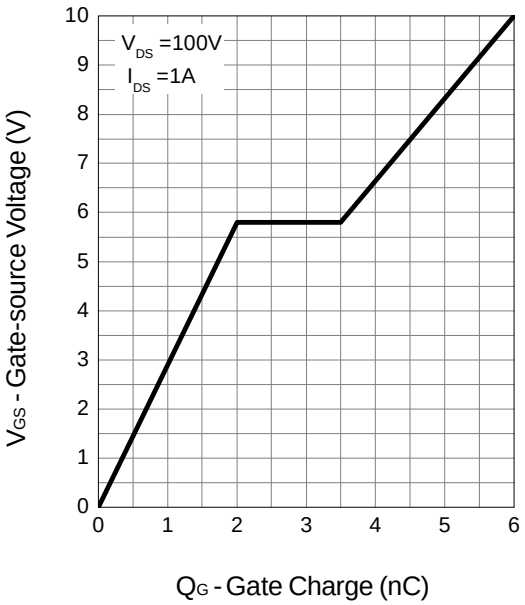
Source-Drain Diode Forward



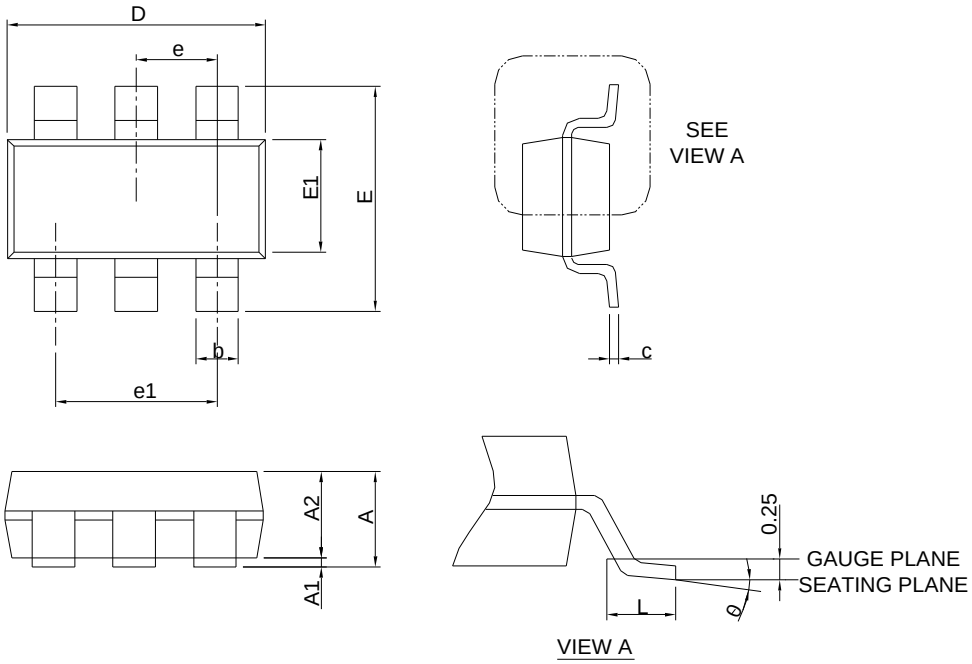
Capacitance



Gate Charge



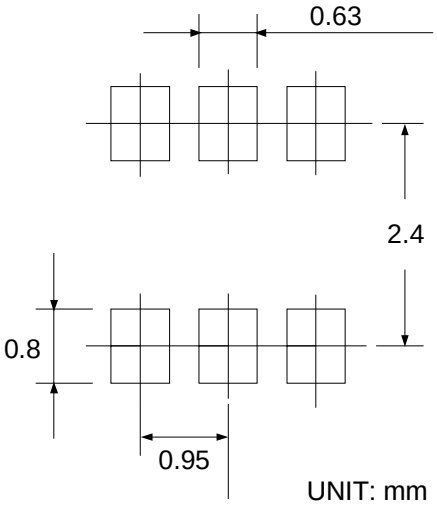
Package Information



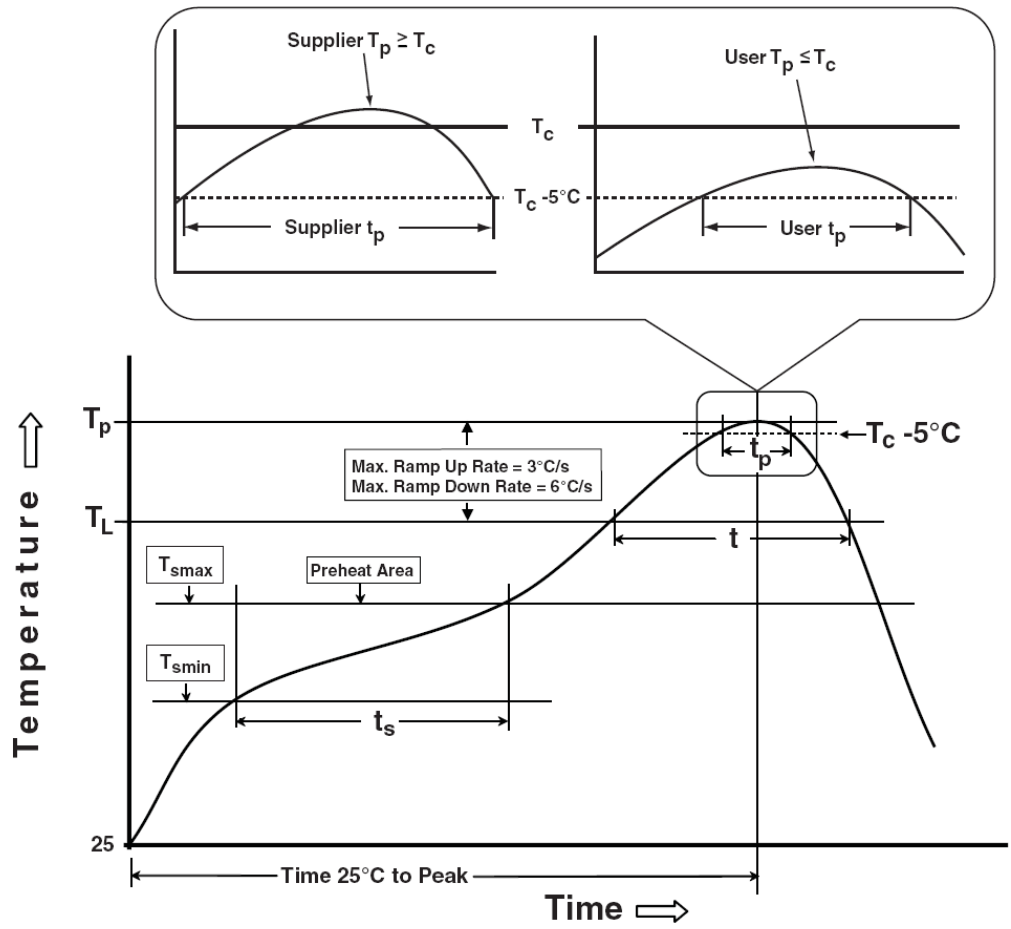
SYMBOL	SOT-23-6			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.25	-	0.049
A1	0.00	0.05	0.000	0.002
A2	0.90	1.20	0.035	0.047
b	0.30	0.50	0.012	0.020
c	0.08	0.22	0.003	0.009
D	2.70	3.10	0.106	0.122
E	2.60	3.00	0.102	0.118
E1	1.40	1.80	0.055	0.071
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
θ	0°	8°	0°	8°

Note : 1. Follow JEDEC TO-178 AB.
2. Dimension D and E1 do not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 10 mil per side.

RECOMMENDED LAND PATTERN



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 ³350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm^3 <350	Volume mm^3 350-2000	Volume mm^3 >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ Tjmax
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ Tjmax
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

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